

Absolute Maximum Ratings ($T_A=25^\circ C$ unless otherwise noted)

| Parameter | Symbol | N-Channel | P-Channel | Unit |
|--|----------------|------------|------------|------|
| Drain-Source Voltage | V_{DS} | 30 | -30 | V |
| Gate-Source Voltage | V_{GS} | ± 20 | ± 20 | V |
| Continuous Drain Current | I_D | 8 | -6 | A |
| Pulsed Drain Current (Note 1) | I_{DM} | 25 | -20 | A |
| Maximum Power Dissipation | P_D | 2.5 | 2.5 | W |
| Operating Junction and Storage Temperature Range | T_J, T_{STG} | -55 To 150 | -55 To 150 | °C |



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SI4542DY-TP

N&P-Channel Complementary MOSFET

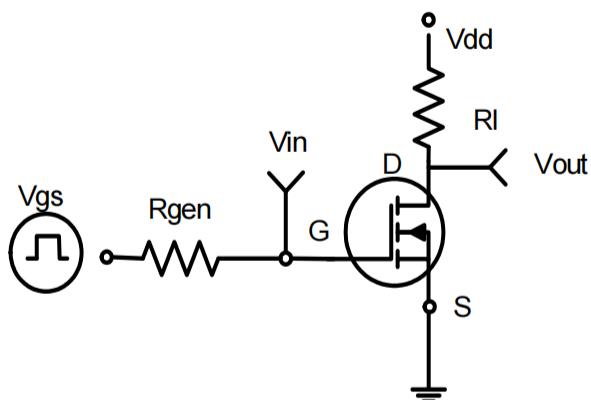
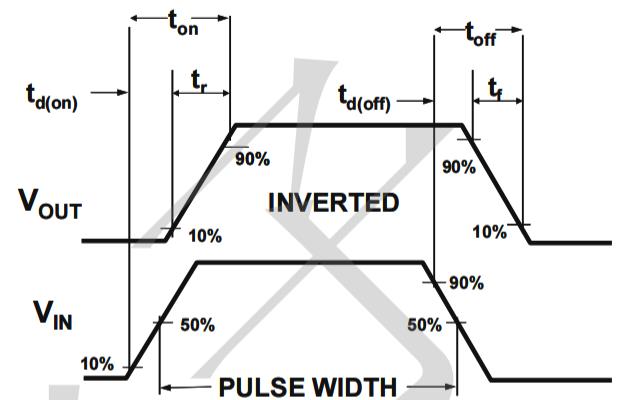
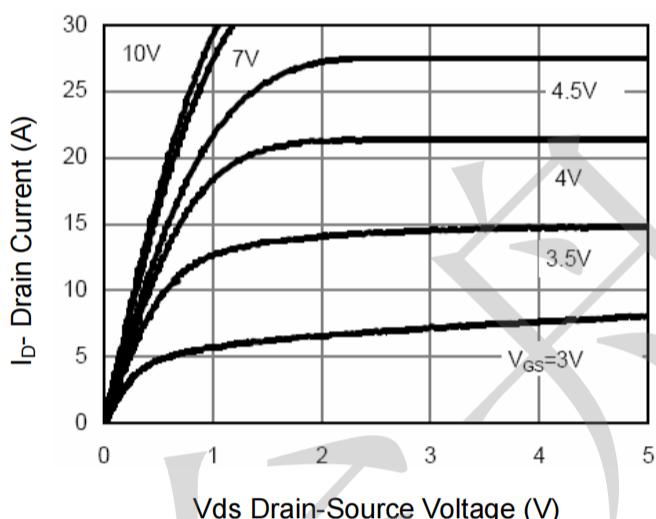
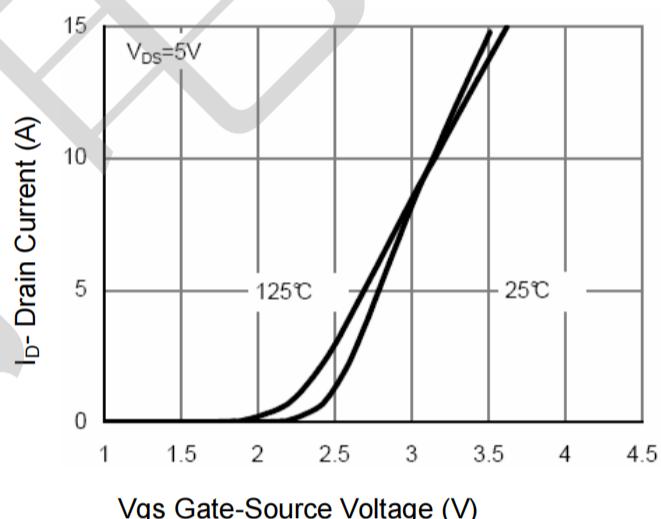
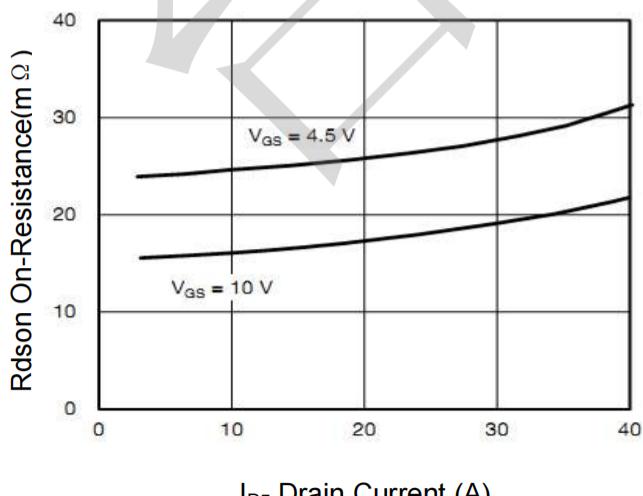
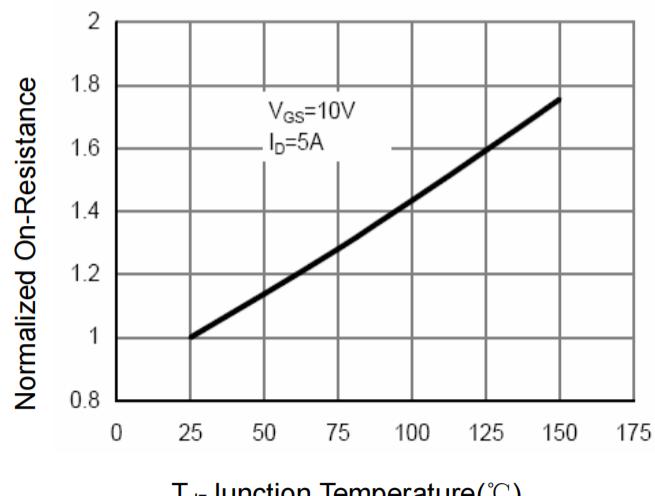
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Thermal Characteristic

| | | | | |
|--|------------------|------|----|------|
| Thermal Resistance,Junction-to-Ambient (Note2) | R _{θJA} | N-Ch | 89 | °C/W |
| | | P-Ch | 90 | |

N-CH Electrical Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)

| Parameter | Symbol | Condition | Min | Typ | Max | Unit |
|---|---------------------|--|-----|------|------|------|
| Off Characteristics | | | | | | |
| Drain-Source Breakdown Voltage | BV _{DSS} | V _{GS} =0V I _D =250μA | 30 | 33 | - | V |
| Zero Gate Voltage Drain Current | I _{DSS} | V _{DS} =24V, V _{GS} =0V | - | - | 1 | μA |
| Gate-Body Leakage Current | I _{GSS} | V _{GS} =±20V, V _{DS} =0V | - | - | ±100 | nA |
| On Characteristics (Note 3) | | | | | | |
| Gate Threshold Voltage | V _{GS(th)} | V _{DS} =V _{GS} , I _D =250μA | 1 | 1.6 | 3 | V |
| Drain-Source On-State Resistance | R _{DS(ON)} | V _{GS} =10V, I _D =6A | - | 17 | 21 | mΩ |
| | | V _{GS} =4.5V, I _D =4A | - | 24 | 31 | mΩ |
| Forward Transconductance | g _{FS} | V _{DS} =5V, I _D =5A | - | 15 | - | S |
| Dynamic Characteristics (Note4) | | | | | | |
| Input Capacitance | C _{iss} | V _{DS} =15V, V _{GS} =0V, F=1.0MHz | - | 480 | - | PF |
| Output Capacitance | C _{oss} | | - | 80 | - | PF |
| Reverse Transfer Capacitance | C _{rss} | | - | 60 | - | PF |
| Switching Characteristics (Note 4) | | | | | | |
| Turn-on Delay Time | t _{d(on)} | V _{DD} =15V, R _L =3Ω V _{GS} =10V, R _{GEN} =3Ω | - | 4.5 | - | nS |
| Turn-on Rise Time | t _r | | - | 2.5 | - | nS |
| Turn-Off Delay Time | t _{d(off)} | | - | 14.5 | - | nS |
| Turn-Off Fall Time | t _f | | - | 3.5 | - | nS |
| Total Gate Charge | Q _g | V _{DS} =15V, I _D =5A, V _{GS} =10V | - | 5.2 | - | nC |
| Gate-Source Charge | Q _{gs} | | - | 0.85 | - | nC |
| Gate-Drain Charge | Q _{gd} | | - | 1.3 | - | nC |
| Drain-Source Diode Characteristics | | | | | | |
| Diode Forward Voltage (Note 3) | V _{SD} | V _{GS} =0V, I _S =3A | - | - | 1.3 | V |
| Diode Forward Current (Note 2) | I _S | | - | - | 4 | A |

N- Channel Typical Electrical and Thermal Characteristics (Curves)

Figure 1:Switching Test Circuit

Figure 2:Switching Waveforms

Figure 3 Output Characteristics

V_{DS}=5V
Figure 4 Transfer Characteristics

I_D- Drain Current (A)
Figure 5 Drain-Source On-Resistance

T_j-Junction Temperature(°C)
Figure 6 Drain-Source On-Resistance



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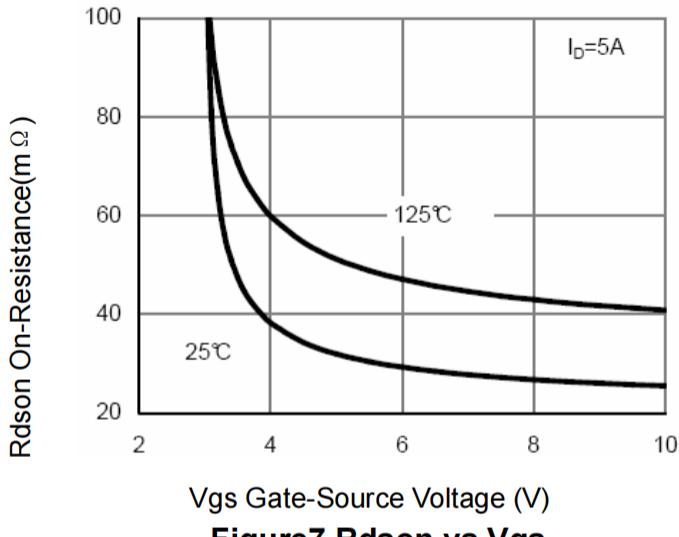


Figure 7 Rdson vs Vgs

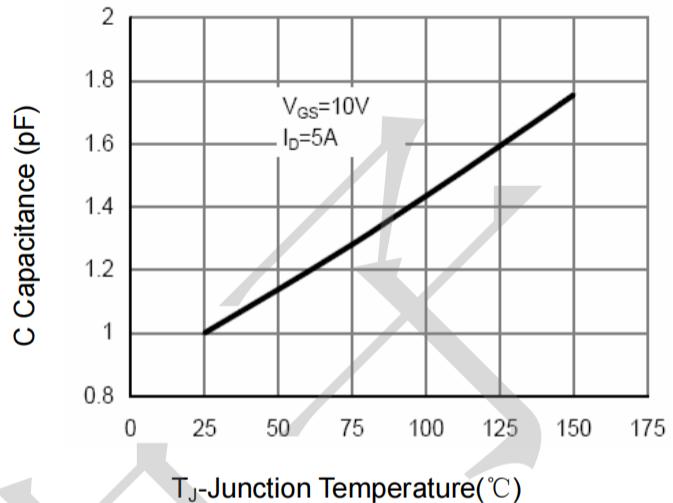


Figure 8 Drain-Source On-Resistance

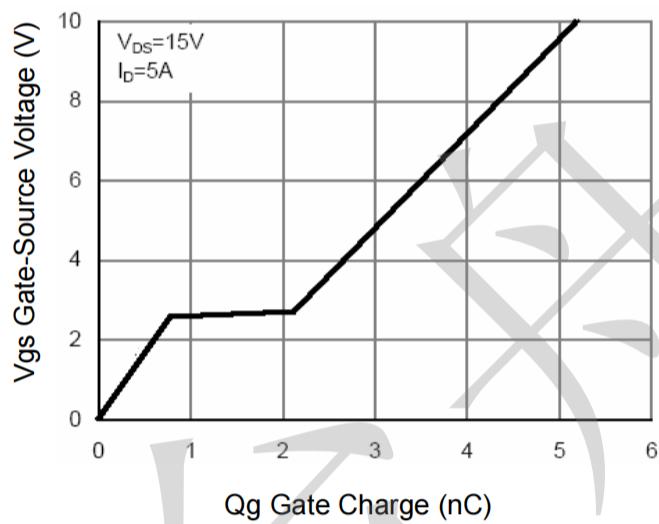


Figure 9 Gate Charge

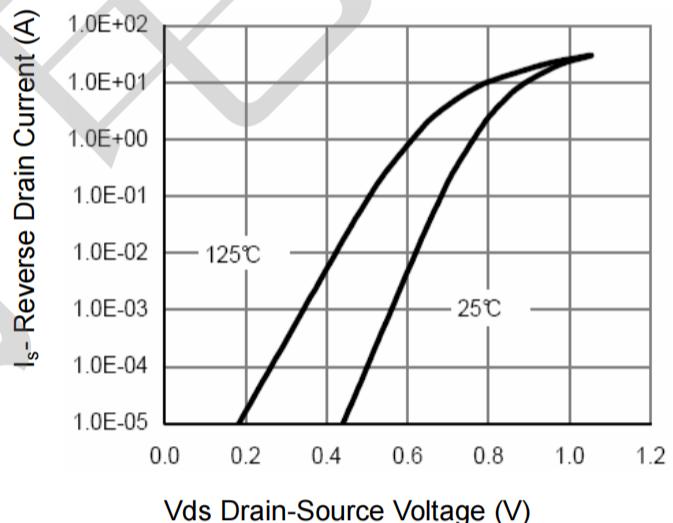


Figure 10 Source-Drain Diode Forward

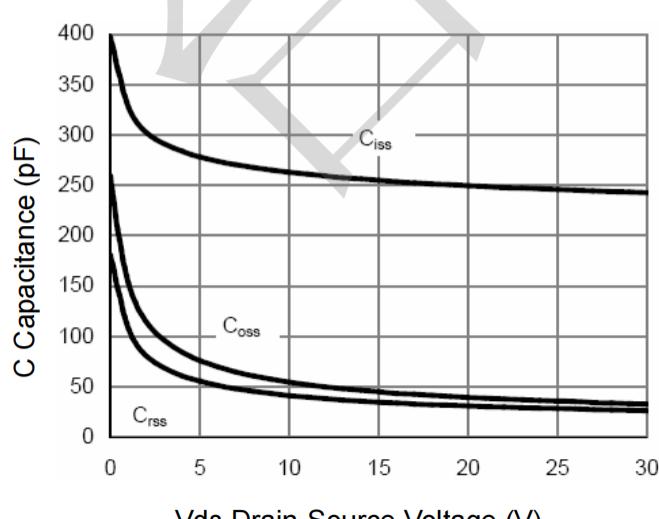


Figure 11 Capacitance vs Vds

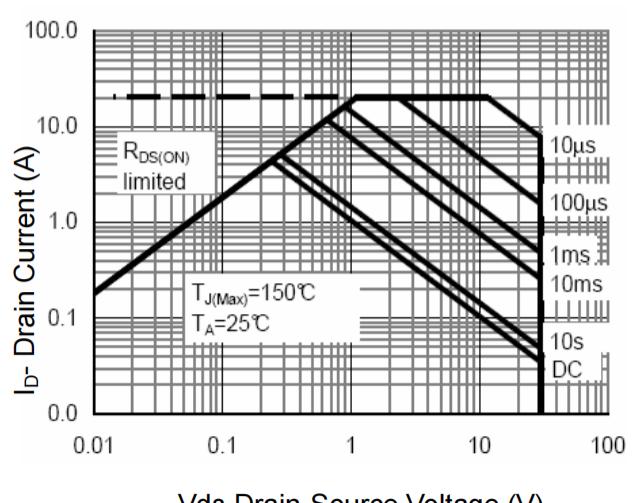


Figure 12 Safe Operation Area

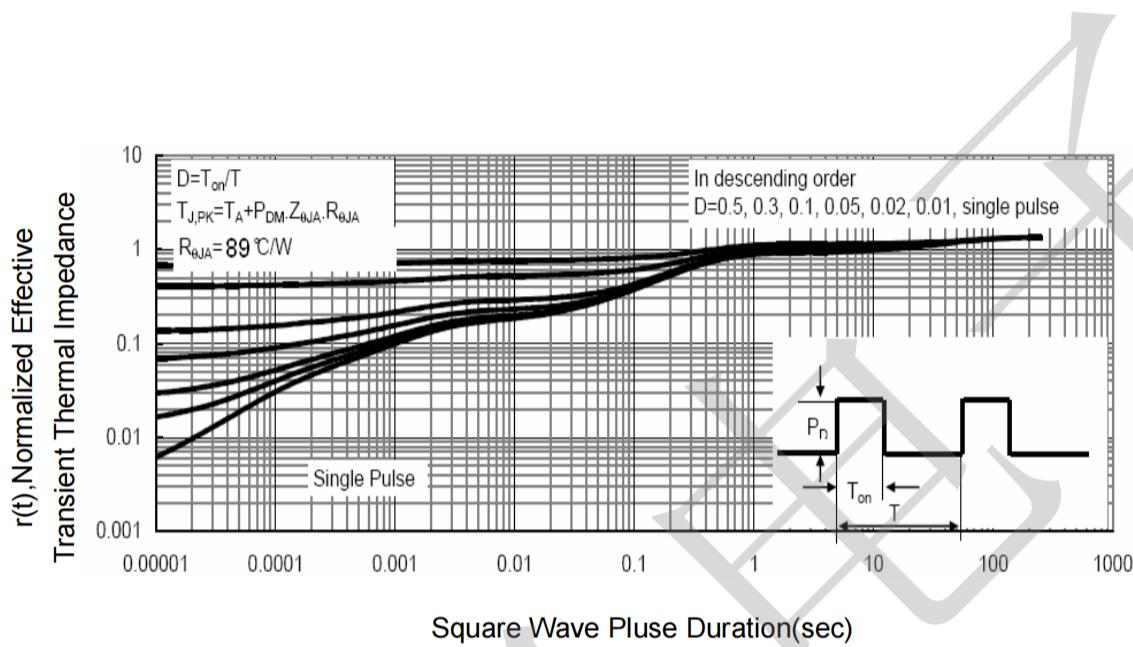


Figure 13 Normalized Maximum Transient Thermal Impedance

P-CH Electrical Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)

| Parameter | Symbol | Condition | Min | Typ | Max | Unit |
|---|----------------------------|--|-----|------|----------|------------------|
| Off Characteristics | | | | | | |
| Drain-Source Breakdown Voltage | BV_{DSS} | $V_{\text{GS}}=0\text{V}, I_{\text{D}}=-250\mu\text{A}$ | -30 | -33 | - | V |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{\text{DS}}=-24\text{V}, V_{\text{GS}}=0\text{V}$ | - | - | -1 | μA |
| Gate-Body Leakage Current | I_{GSS} | $V_{\text{GS}}=\pm20\text{V}, V_{\text{DS}}=0\text{V}$ | - | - | ±100 | nA |
| On Characteristics (Note 3) | | | | | | |
| Gate Threshold Voltage | $V_{\text{GS}(\text{th})}$ | $V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=-250\mu\text{A}$ | -1 | -1.5 | -2 | V |
| Drain-Source On-State Resistance | $R_{\text{DS}(\text{ON})}$ | $V_{\text{GS}}=-10\text{V}, I_{\text{D}}=-5\text{A}$ | - | 40 | 50 | $\text{m}\Omega$ |
| | | $V_{\text{GS}}=-4.5\text{V}, I_{\text{D}}=-4\text{A}$ | - | 60 | 75 | $\text{m}\Omega$ |
| Forward Transconductance | g_{FS} | $V_{\text{DS}}=-5\text{V}, I_{\text{D}}=-4.1\text{A}$ | 5.5 | - | - | S |
| Dynamic Characteristics (Note 4) | | | | | | |
| Input Capacitance | C_{iss} | $V_{\text{DS}}=-15\text{V}, V_{\text{GS}}=0\text{V}, F=1.0\text{MHz}$ | - | 648 | - | PF |
| Output Capacitance | C_{oss} | | - | 108 | - | PF |
| Reverse Transfer Capacitance | C_{rss} | | - | 68 | - | PF |
| Switching Characteristics (Note 4) | | | | | | |
| Turn-on Delay Time | $t_{\text{d(on)}}$ | $V_{\text{DD}}=-15\text{V}, R_{\text{L}}=3.6\Omega$ $V_{\text{GS}}=-10\text{V}, R_{\text{GEN}}=3\Omega$ | - | 9 | - | nS |
| Turn-on Rise Time | t_r | | - | 5 | - | nS |
| Turn-Off Delay Time | $t_{\text{d(off)}}$ | | - | 28 | - | nS |
| Turn-Off Fall Time | t_f | | - | 13.5 | - | nS |
| Total Gate Charge | Q_g | $V_{\text{DS}}=-15\text{V}, I_{\text{D}}=-4\text{A}, V_{\text{GS}}=-10\text{V}$ | - | 14 | - | nC |
| Gate-Source Charge | Q_{gs} | | - | 3.1 | - | nC |
| Gate-Drain Charge | Q_{gd} | | - | 3. | - | nC |
| Drain-Source Diode Characteristics | | | | | | |
| Diode Forward Voltage (Note 3) | V_{SD} | $V_{\text{GS}}=0\text{V}, I_{\text{s}}=-1\text{A}$ | - | - | -1.3 | V |

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production

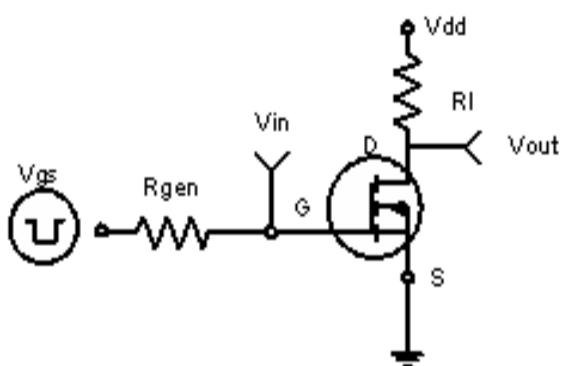
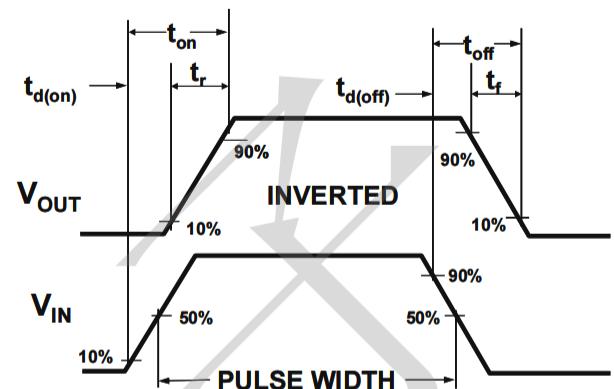
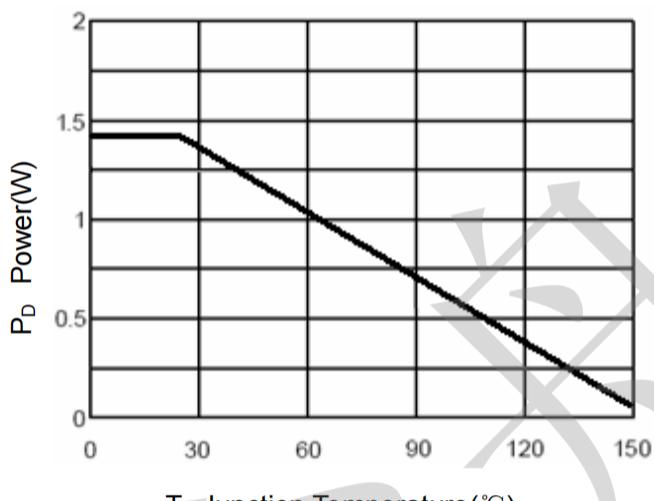
P-Channel Typical Electrical and Thermal Characteristics

Figure 1:Switching Test Circuit

Figure 2:Switching Waveforms

 T_j-Junction Temperature(°C)

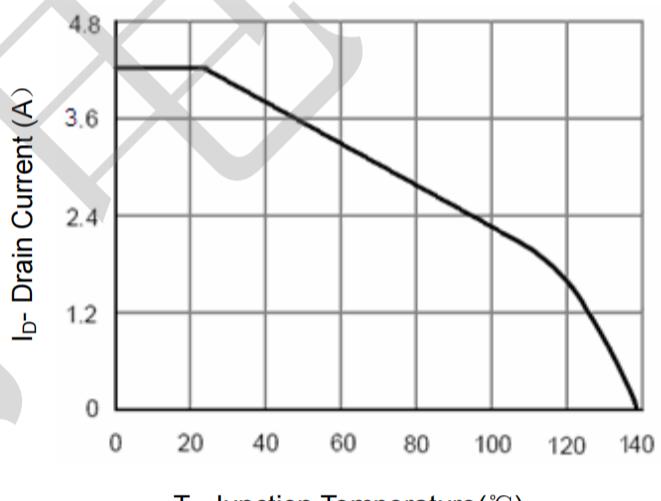
Figure 3 Power Dissipation

 T_j-Junction Temperature(°C)

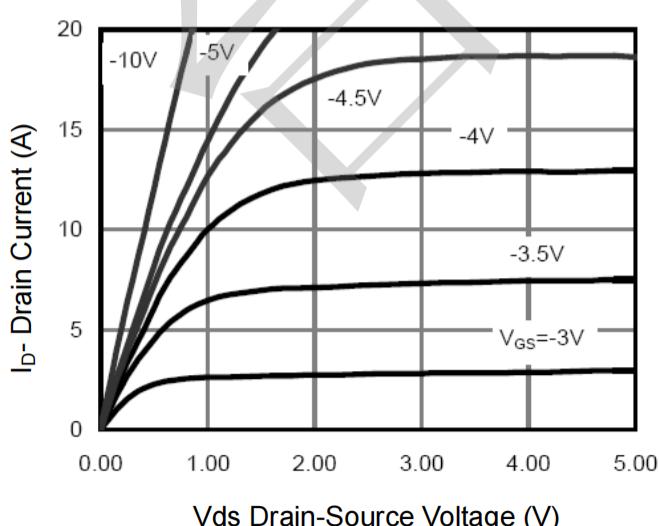
Figure 4 Drain Current

 V_{ds} Drain-Source Voltage (V)

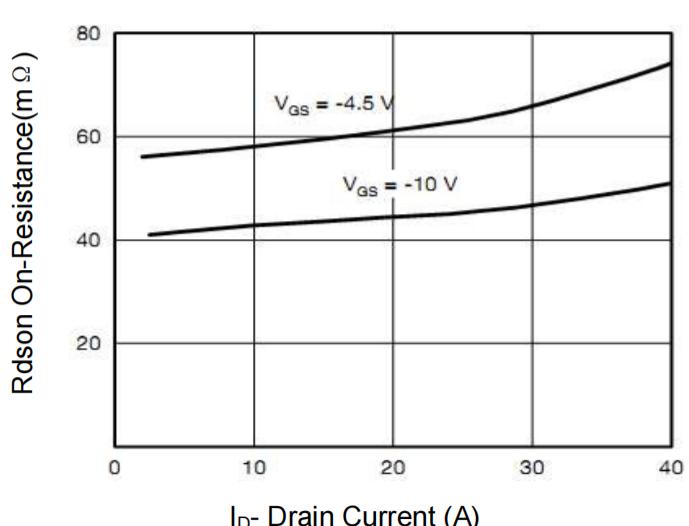
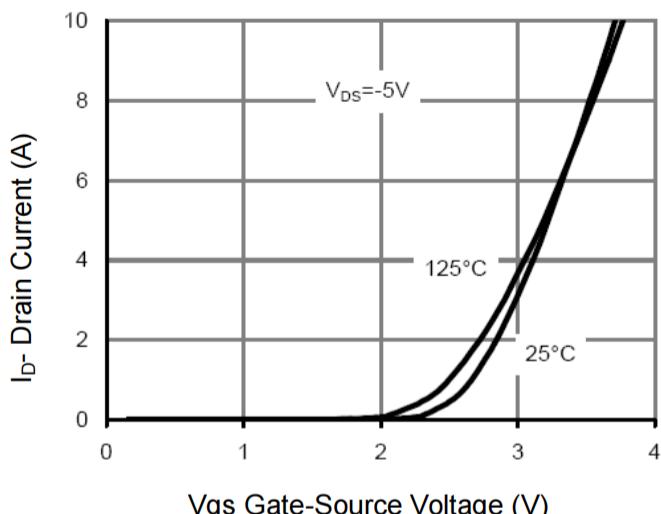
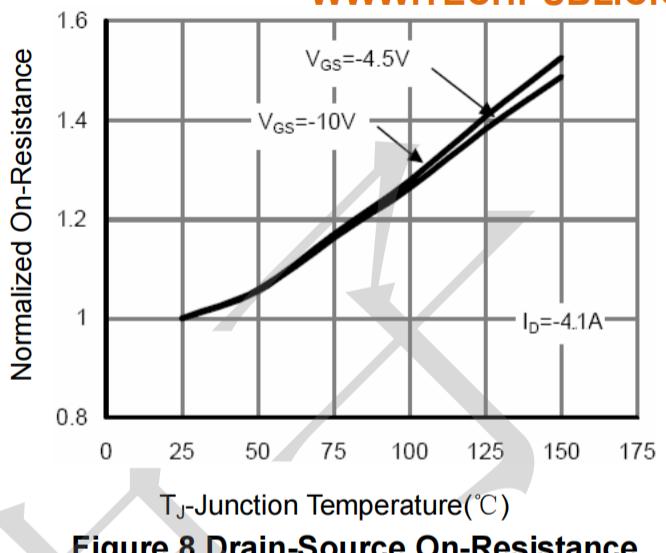
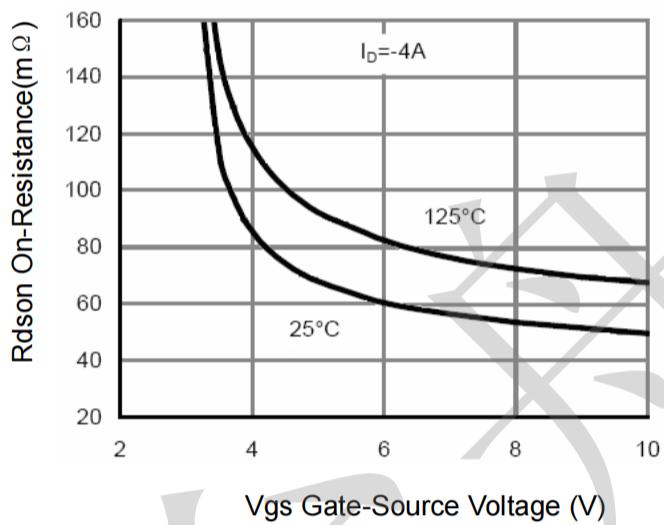
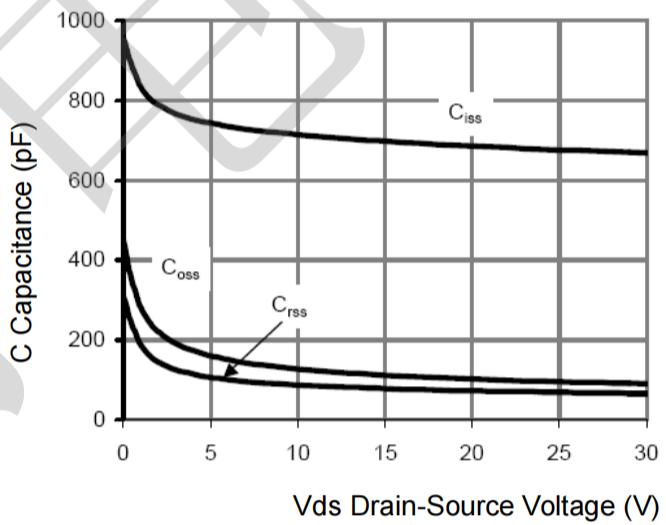
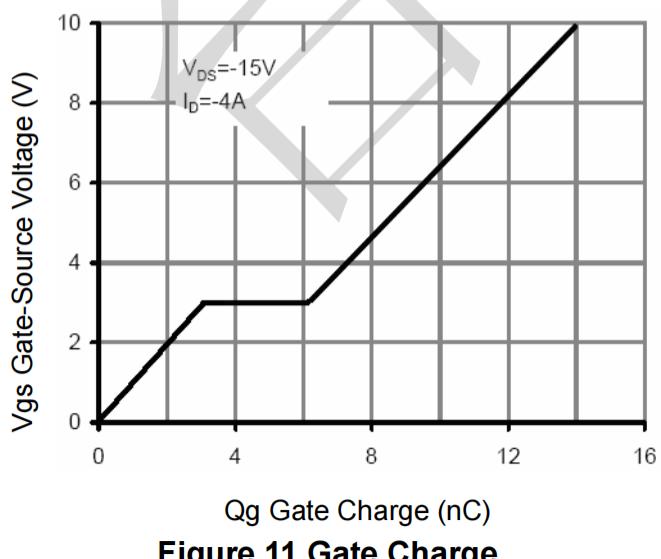
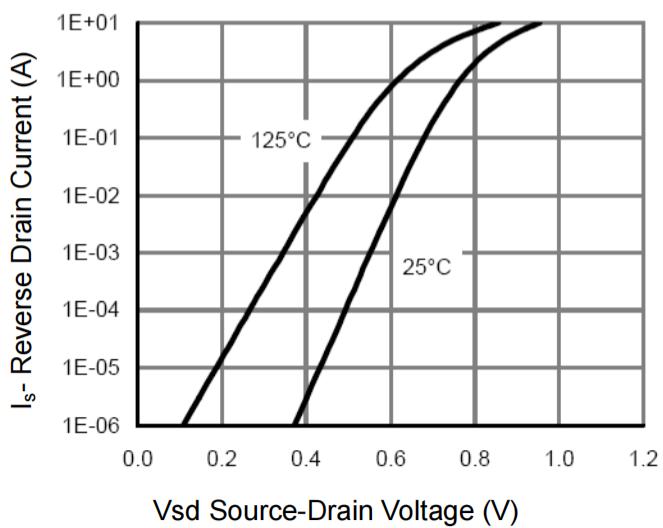
Figure 5 Output CHARACTERISTICS

 I_D- Drain Current (A)

Figure 6 Drain-Source On-Resistance


Figure 7 Transfer Characteristics

Figure 8 Drain-Source On-Resistance

Figure 9 R_{DSON} vs V_{GS}

Figure 10 Capacitance vs V_{DS}

Figure 11 Gate Charge

Figure 12 Source-Drain Diode Forward



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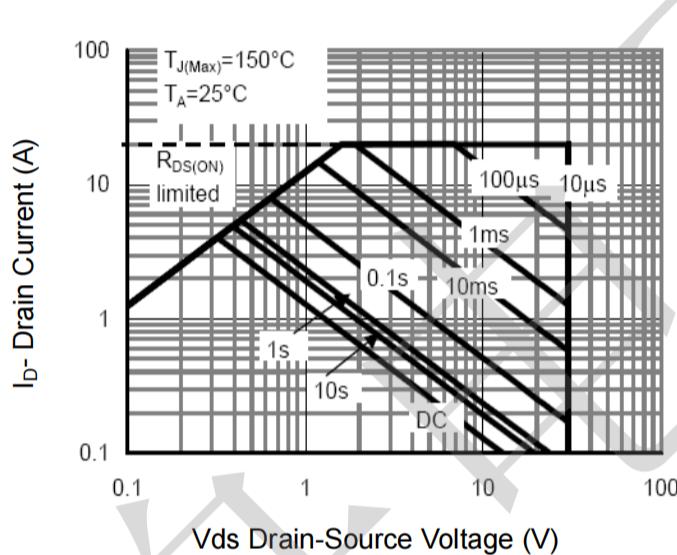


Figure 13 Safe Operation Area

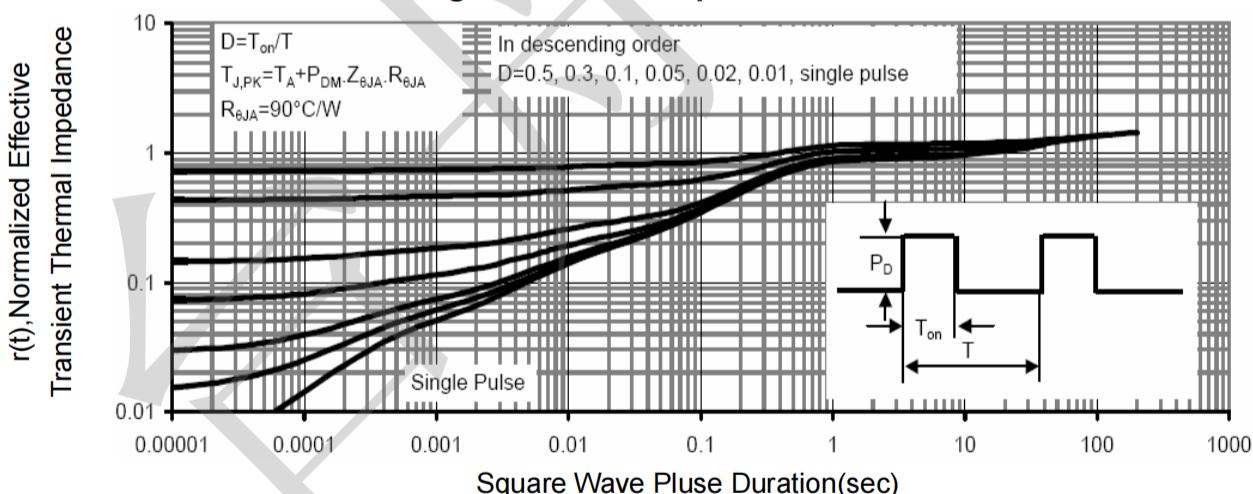
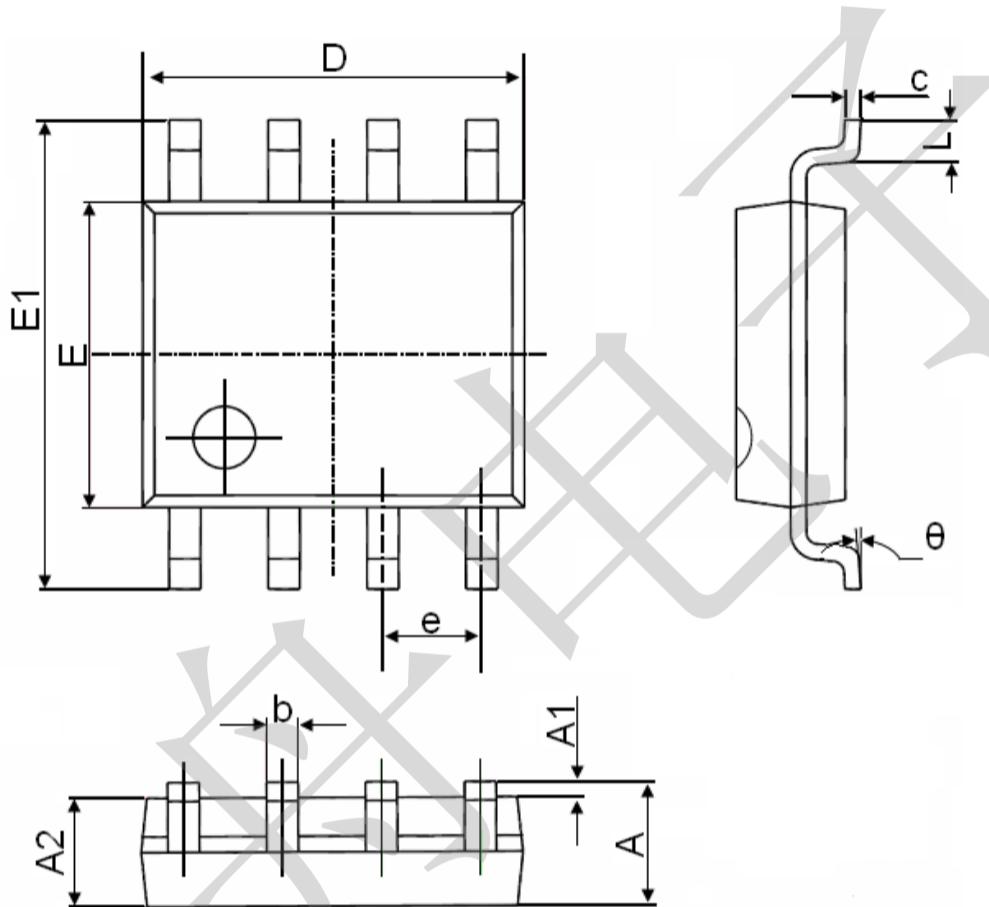


Figure 14 Normalized Maximum Transient Thermal Impedance



SOP-8 Package Information



| Symbol | Dimensions In Millimeters | | Dimensions In Inches | |
|--------|---------------------------|-------|----------------------|-------|
| | Min. | Max. | Min. | Max. |
| A | 1.350 | 1.750 | 0.053 | 0.069 |
| A1 | 0.100 | 0.250 | 0.004 | 0.010 |
| A2 | 1.350 | 1.550 | 0.053 | 0.061 |
| b | 0.330 | 0.510 | 0.013 | 0.020 |
| c | 0.170 | 0.250 | 0.006 | 0.010 |
| D | 4.700 | 5.100 | 0.185 | 0.200 |
| E | 3.800 | 4.000 | 0.150 | 0.157 |
| E1 | 5.800 | 6.200 | 0.228 | 0.244 |
| e | 1.270(BSC) | | 0.050(BSC) | |
| L | 0.400 | 1.270 | 0.016 | 0.050 |
| θ | 0° | 8° | 0° | 8° |